

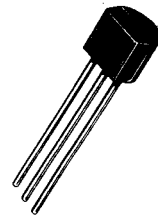
MPS6520, MPS6521 NPN (SILICON) MPS6522, MPS6523 PNP

SILICON ANNULAR TRANSISTORS

... designed for general-purpose amplifier applications and for complementary circuitry.

- High DC Current Gain –
hFE = 150 (Min) @ IC = 100 μAdc – MPS6521, MPS6523
- Low Noise Figure –
NF = 1.8 dB (Typ) @ IC = 10 μAdc
- Low Output Capacitance –
Cob = 3.5 pF (Max) @ VCB = 10 Vdc

SILICON COMPLEMENTARY AMPLIFIER TRANSISTORS

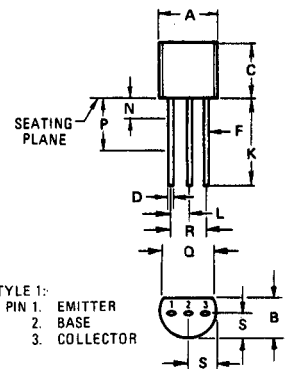


MAXIMUM RATING

Rating	Symbol	NPN	PNP	Unit
Collector-Emitter Voltage MPS6520, MPS6521 MPS6522, MPS6523	V _{CEO}	25	25	Vdc
Collector-Base Voltage MPS6520, MPS6521 MPS6522, MPS6523	V _{CB}	40	25	Vdc
Emitter-Base Voltage	V _{EB}	4.0	4.0	Vdc
Collector Current – Continuous	I _C	100	100	mAdc
Total Power Dissipation @ T _A = 25°C Derate above 25°C	P _D	350 2.81	350 2.81	mW mW/°C
Total Power Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.0 8.0	1.0 8.0	Watt mW/°C
Operating Junction Temperature Range	T _J	150	150	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient (Printed Circuit Board Mounting)	R _{θJA}	357	°C/ W
Thermal Resistance, Junction to Case	R _{θJC}	125	°C/ W



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.450	5.200	0.175	0.205
B	3.180	4.190	0.125	0.210
C	4.320	5.330	0.170	0.210
D	0.407	0.533	0.016	0.021
F	0.407	0.482	0.016	0.019
K	12.700	–	0.500	–
L	1.150	1.390	0.045	0.055
N	–	1.270	–	0.050
P	6.350	–	0.250	–
Q	3.430	–	0.135	–
R	2.410	2.670	0.095	0.105
S	2.030	2.670	0.080	0.105

CASE 29-02
TO-92